kyu-seung Lee

List of Publications by Year
in descending order

18	211	1307594	996975
papers	citations	7	15
		h-index	g-index

19	19	19	297
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	White light emitting diodes realized by using an active packaging method with CdSe/ZnS quantum dots dispersed in photosensitive epoxy resins. Nanotechnology, 2008, 19, 145202.	2.6	60
2	Spatial correlation between optical properties and defect formation in GaN thin films laterally overgrown on cone-shaped patterned sapphire substrates. Journal of Applied Physics, 2010, 107, .	2.5	34
3	Active Packaging Method for Light-Emitting Diode Lamps With Photosensitive Epoxy Resins. IEEE Photonics Technology Letters, 2008, 20, 87-89.	2.5	17
4	Influence of defect reduction and strain relaxation on carrier dynamics in InGaN-based light-emitting diodes on cone-shaped patterned sapphire substrates. Journal of Applied Physics, 2013, 113, .	2.5	15
5	Phosphor-free white-light emitters using in-situ GaN nanostructures grown by metal organic chemical vapor deposition. Scientific Reports, 2015, 5, 17372.	3.3	14
6	Self-assembled growth of inclined GaN nanorods on (10â˜10) m-plane sapphire using metalâ€“organic chemical vapor deposition. Journal of Crystal Growth, 2015, 409, 65-70.	1.5	12
7	Defect reduction of SiN x embedded m -plane GaN grown by hydride vapor phase epitaxy. Journal of Crystal Growth, 2014, 407, 6-10.	1.5	10
8	Colour-crafted phosphor-free white light emitters via in-situ nanostructure engineering. Scientific Reports, 2017, 7, 44148.	3.3	8
9	Active packing method for blue light-emitting diodes with photosensitive polymerization: formation of self-focusing encapsulates. Optics Express, 2008, 16, 3680.	3.4	7
10	Fabrication of sharp-needled conical polymer tip on the cross-section of optical fiber via two-photon polymerization for tuning-fork-based atomic force microscopy. Optics Communications, 2013, 286, 197-203.	2.1	7
11	Fabrication of CdSeâ€“ZnS nanocrystal-based local fluorescent aperture probes by active polymerization of photosensitive epoxy. Optics Communications, 2008, 281, 1588-1592.	2.1	6
12	Inclined angle-controlled growth of GaN nanorods onm-sapphire by metal organic chemical vapor deposition without a catalyst. Nanotechnology, 2015, 26, 335601.	2.6	6
13	Strain relaxation of thick (11â€“22) semipolar InGaN layer for long wavelength nitride-based device. Journal of Applied Physics, 2014, 116, 163109.	2.5	4
14	Functionalized inclined-GaN based nanoneedles. Journal of Industrial and Engineering Chemistry, 2018, 59, 184-191.	5.8	4
15	Semipolar (11â€“22) InGaN-Based Light-Emitting Diodes with Low Defects Grown on m-Plane Sapphire Using Metalorganic Chemical Vapor Epitaxy. Journal of Nanoscience and Nanotechnology, 2016, 16, 10881-10886.	0.9	3
16	Comparison between the relaxation mechanisms of thick (0001) polar and $(11ar{2}2)$ semipolar InGaN layers. Japanese Journal of Applied Physics, 2015, 54, 02BA02.	1.5	2
17	Growth of Semipolar InGaN Quantum Well Structure Using Self-Organized Nano-Masks on <I>m</I>-Sapphire. Journal of Nanoscience and Nanotechnology, 2013, 13, 6429-6433.	0.9	1
18	Self-assembled growth and structural analysis of inclined GaN nanorods on nanoimprinted m-sapphire using catalyst-free metal-organic chemical vapor deposition. AIP Advances, 2016, 6, 045209.	1.3	1